MMG100S120B6HN

1200V 100A IGBT Module

April 2015 **Version 01** **RoHS Compliant**

PRODUCT FEATURES

☐ High short circuit capability,self limiting short circuit current

☐ IGBT CHIP(T4 Fast Trench+Field Stop technology)

☐ $V_{CE(sat)}$ with positive temperature coefficient

☐ Fast switching and short tail current

☐ Free wheeling diodes with fast and soft reverse recovery

☐ Low switching losses

☐ T_{Jmax} =175°C

APPLICATIONS

☐ High frequency switching application

☐ Medical applications

☐ Motion/servo control

☐ UPS systems

IGBT-inverter

ABSOLUTE MAXIMUM RATINGS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	T_J=25℃	1200	V
V_{GES}	Gate Emitter Voltage		±20	
I_C	DC Collector Current	T_C=25℃	150	A
		T_C=95℃	100	
I_{CM}	Repetitive Peak Collector Current	tp=1ms	200	
P_{tot}	Power Dissipation Per IGBT		550	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	T_J=25℃	1200	V
$I_{F(AV)}$	Average Forward Current	T_C=25℃	100	A
I_{FRM}	Repetitive Peak Forward Current	tp=1ms	200	
I^2t		T_J =125℃, t=10ms, V_R=0V	1850	A^2S

IGBT-inverter
ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions			Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	V_{CE}=V_{GE}, I_C=4mA		5.4	6.0	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	I_C=100A, V_{GE}=15V, T_J=25℃			2.1	2.5	
		I_C=100A, V_{GE}=15V, T_J=125℃			2.5		
I_{CES}	Collector Leakage Current	V_{CE}=1200V, V_{GE}=0V, T_J=25℃				1	mA
		V_{CE}=1200V, V_{GE}=0V, T_J=125℃				10	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V,V_{GE}=±15V, T_J=25℃		-400		400	nA
R_{gint}	Integrated Gate Resistor				7.5		Ω
Q_g	Gate Charge	V_{CE}=600V, I_C=100A , V_{GE}=15V			0.47		µC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			6.2		nF
C_{res}	Reverse Transfer Capacitance				350		pF
$t_{d(on)}$	Turn on Delay Time	V_{CC}=600V,I_C=100A R_G =7.5Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		150		ns
			T_J=125℃		160		ns
			T_J=150℃		170		ns
t_r	Rise Time		T_J=25℃		65		ns
			T_J=125℃		70		ns
			T_J=150℃		75		ns
$t_{d(off)}$	Turn off Delay Time	V_{CC}=600V,I_C=100A R_G =7.5Ω, V_{GE}=±15V, Inductive Load	T_J=25℃		400		ns
			T_J=125℃		450		ns
			T_J=150℃		480		ns
t_f	Fall Time		T_J=25℃		40		ns
			T_J=125℃		60		ns
			T_J=150℃		70		ns
E_{on}	Turn on Energy	V_{CC}=600V,I_C=100A R_G =7.5Ω, V_{GE}=±15V, Inductive Load	T_J=125℃		11.5		mJ
			T_J=150℃		12.5		mJ
E_{off}	Turn off Energy		T_J=125℃		5.5		mJ
			T_J=150℃		6.0		mJ
I_{SC}	Short Circuit Current	tpsc≤10µS , V_{GE}=15V T_J=125℃,V_{CC}=600V			400		A
R_{thJC}	Junction to Case Thermal Resistance （ Per IGBT）					0.27	K /W

Diode-inverter
ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	I_F=100A , V_{GE}=0V, T_J=25℃		1.65	2.15	V
		I_F=100A , V_{GE}=0V, T_J=125℃		1.65		
t_{rr}	Reverse Recovery Time	I_F=100A , V_R=600V dI_F/dt=-1500A/µs T_J =125℃		480		ns
I_{RRM}	Max. Reverse Recovery Current			85		A
Q_{RR}	Reverse Recovery Charge			19.4		µC
E_{rec}	Reverse Recovery Energy			7.6		mJ
R_{thJCD}	Junction to Case Thermal Resistance （ Per Diode）				0.5	K /W

MODULE CHARACTERISTICS

T_C=25°C unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		175	℃
T_{Jop}	Operating Temperature		-40~150	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
CTI	Comparative Tracking Index		＞200	
Torque	to heatsink	Recommended（M6）	3~5	Nm
	to terminal	Recommended（M5）	2.5~5	Nm
Weight			160	g

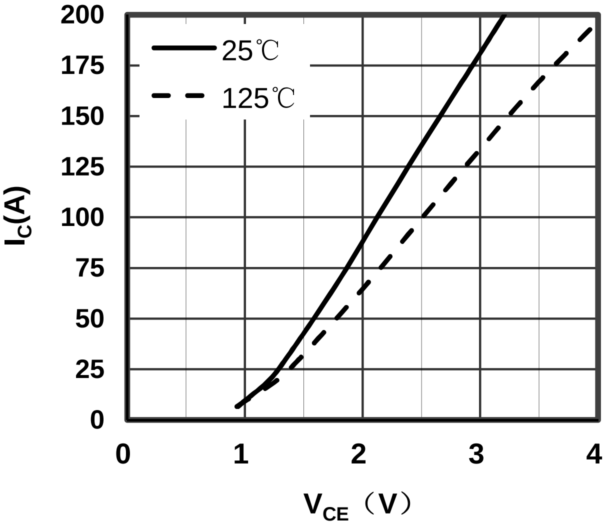


Figure 1. Typical Output Characteristics IGBT-inverter

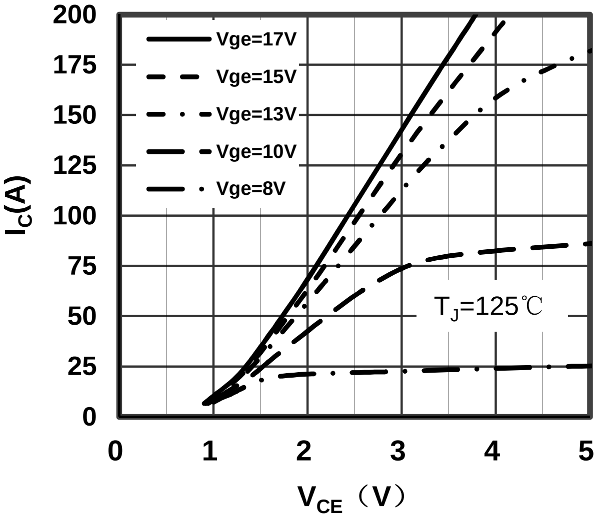


Figure 2. Typical Output Characteristics IGBT-inverter

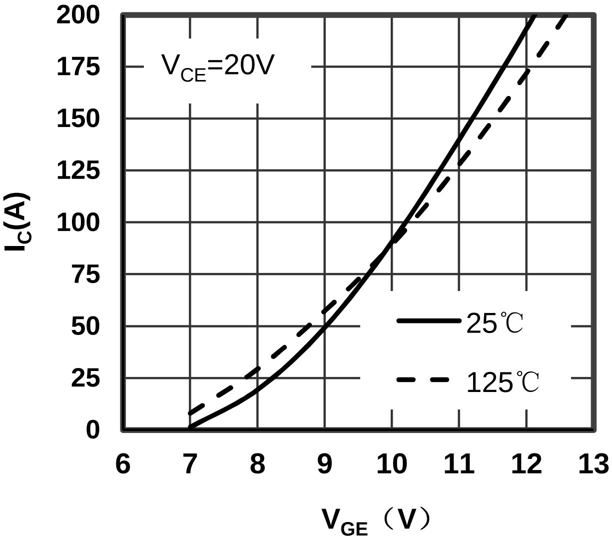


Figure 3. Typical Transfer characteristics IGBT-inverter

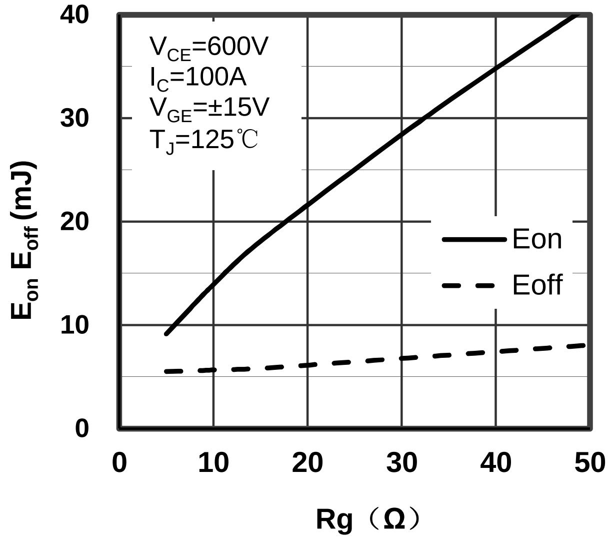


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

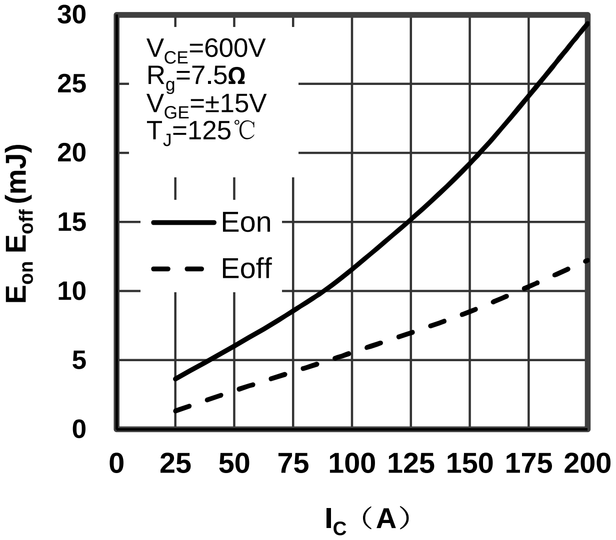


Figure 5. Switching Energy vs Collector Current
IGBT-inverter

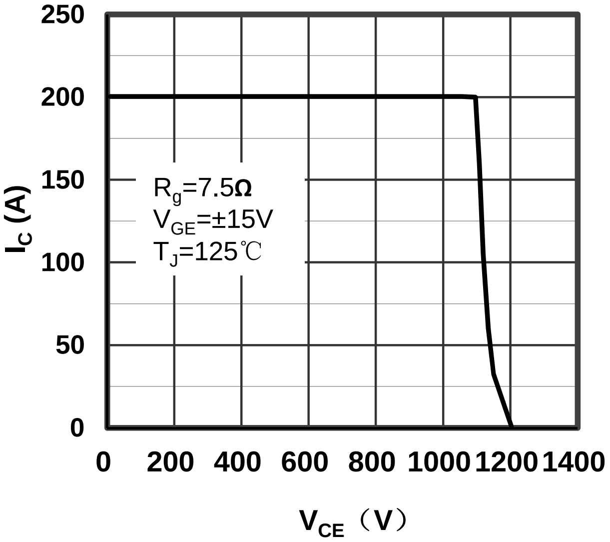


Figure 6. Reverse Biased Safe Operating Area
IGBT-inverter

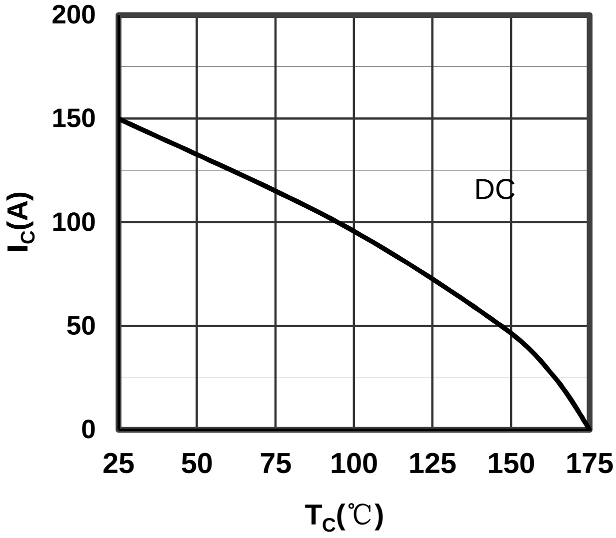


Figure 7. Collector Current vs Case temperature
IGBT -inverter

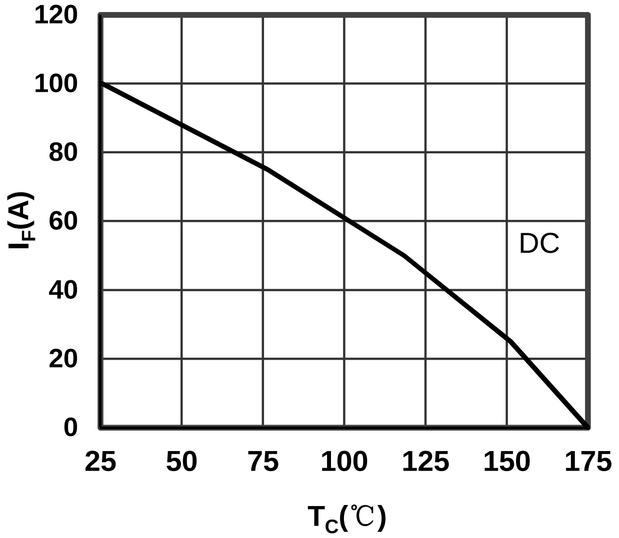


Figure 8. Forward current vs Case temperature
Diode -inverter

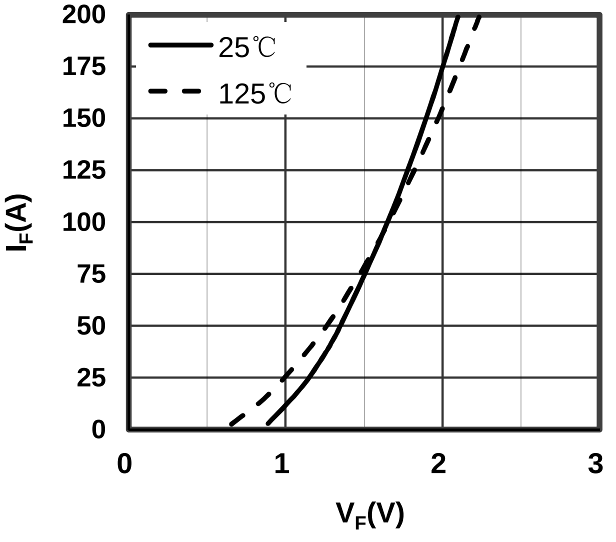


Figure 9. Diode Forward Characteristics
Diode -inverter

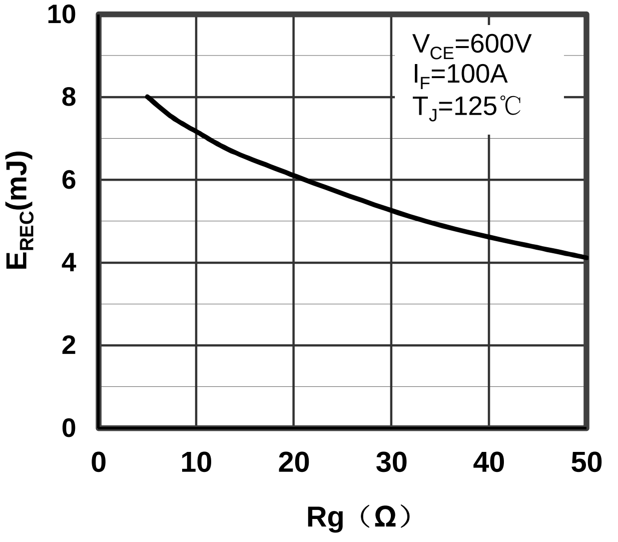


Figure 10. Switching Energy vs Gate Resistor
Diode -inverter

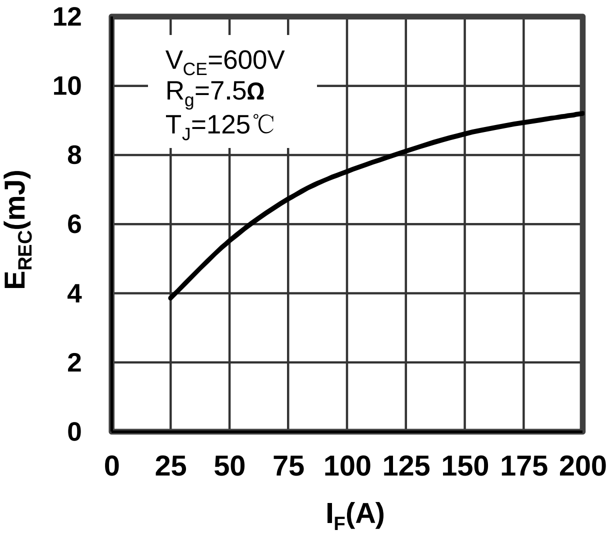


Figure 11. Switching Energy vs Forward Current Diode-inverter

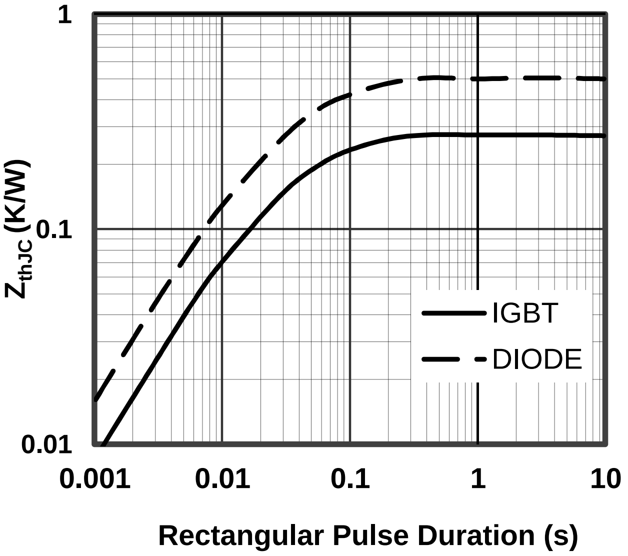


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

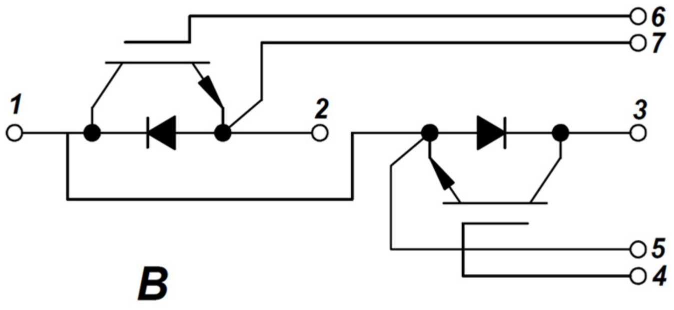
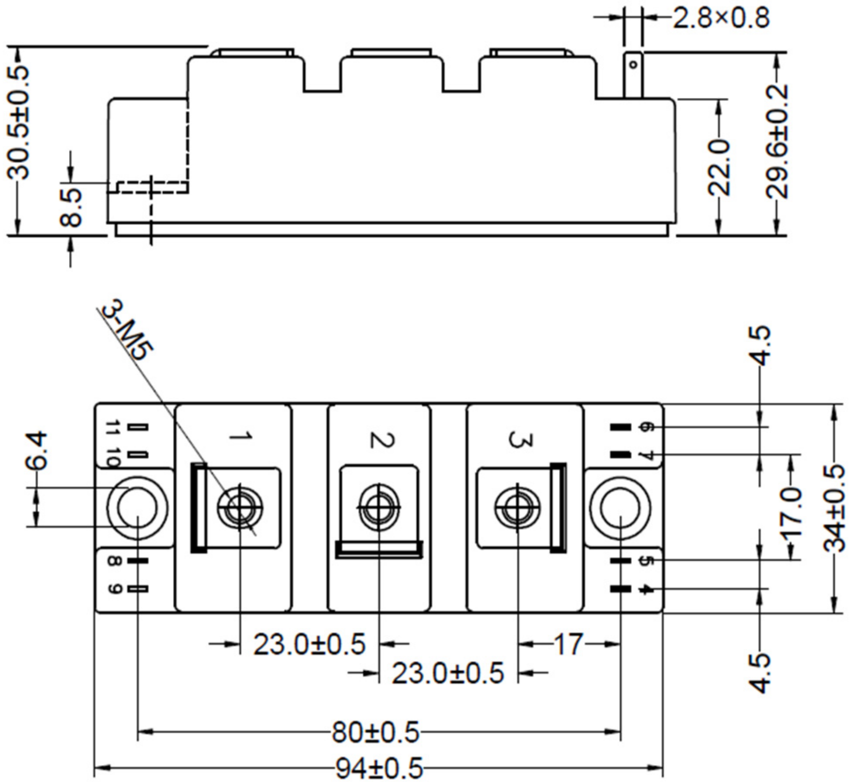


Figure 13. Circuit Diagram



Dimensions in (mm)

Figure 14. Package Outline